International TOR Rectifier

HFA16TB120

$HEXFRED^{\mathsf{TM}}$

Ultrafast, Soft Recovery Diode

Features

- · Ultrafast Recovery
- Ultrasoft Recovery
- Very Low I_{RRM}
- · Very Low Qrr
- · Specified at Operating Conditions

Benefits

- · Reduced RFI and EMI
- Reduced Power Loss in Diode and Switching Transistor
- · Higher Frequency Operation
- Reduced Snubbing
- · Reduced Parts Count

$V_R = 1200V$ $V_F(typ.)^* = 2.3V$ $I_{F(AV)} = 16A$ $Q_{rr}(typ.) = 260nC$ $I_{RRM}(typ.) = 5.8A$ $t_{rr}(typ.) = 30ns$ $di_{(rec)M}/dt(typ.)^* = 76A/\mu s$



Description

International Rectifier's HFA16TB120 is a state of the art ultra fast recovery diode. Employing the latest in epitaxial construction and advanced processing techniques it features a superb combination of characteristics which result in performance which is unsurpassed by any rectifier previously available. With basic ratings of 1200 volts and 16 amps continuous current, the HFA16TB120 is especially well suited for use as the companion diode for IGBTs and MOSFETs. In addition to ultra fast recovery time, the HEXFRED product line features extremely low values of peak recovery current (I_{RRM}) and does not exhibit any tendency to "snap-off" during the tb portion of recovery. The HEXFRED features combine to offer designers a rectifier with lower noise and significantly lower switching losses in both the diode and the switching transistor. These HEXFRED advantages can help to significantly reduce snubbing, component count and heatsink sizes. The HEXFRED HFA16TB120 is ideally suited for applications in power supplies and power conversion systems (such as inverters), motor drives, and many other similar applications where high speed, high efficiency is needed.

Absolute Maximum Ratings

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	Parameter	Max	Units	
V _R	Cathode-to-Anode Voltage	1200	V	
I _F @ T _C = 100°C	Continuous Forward Current	16		
I _{FSM}	Single Pulse Forward Current	190	Α	
I _{FRM}	Maximum Repetitive Forward Current	64		
P _D @ T _C = 25°C	Maximum Power Dissipation	151	- °C	
P _D @ T _C = 100°C	Maximum Power Dissipation	60	7 .	
TJ	Operating Junction and	FF to 1450	W	
T _{STG}	Storage Temperature Range	-55 to +150		

^{* 125°}C



Electrical Characteristics @ T_J = 25°C (unless otherwise specified)

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Parameter	Min	Тур	Max	Units	Test Conditions	
Cathode Anode Breakdown Voltage	1200			V	I _R = 100μA	
Max Forward Voltage		2.5	3.0		I _F = 16A	
		3.2	3.93	V	I _F = 32A See Fig. 1	
		2.3	2.7		I _F = 16A, T _J = 125°C	
Max Reverse Leakage Current		0.75	20	μA	$V_R = V_R$ Rated See Fig. 2	
		375	2000		T _J = 125°C, V _R = 0.8 x V _R Rated	
Junction Capacitance		27	40	pF	V _R = 200V See Fig. 3	
Series Inductance		8.0		nH	Measured lead to lead 5mm from	
					package body	
	Cathode Anode Breakdown Voltage Max Forward Voltage Max Reverse Leakage Current Junction Capacitance	Cathode Anode Breakdown Voltage Max Forward Voltage Max Reverse Leakage Current Junction Capacitance	Cathode Anode Breakdown Voltage 1200 2.5 3.2 2.3	Cathode Anode Breakdown Voltage 1200 Max Forward Voltage 2.5 3.0 Max Forward Voltage 3.2 3.93 2.3 2.7 0.75 20 Max Reverse Leakage Current 375 2000 Junction Capacitance 27 40	Cathode Anode Breakdown Voltage 1200 V Max Forward Voltage 2.5 3.0 3.2 3.93 V 2.3 2.7 Max Reverse Leakage Current 0.75 20 375 2000 Junction Capacitance 27 40 pF	

Dynamic Recovery Characteristics @ T_J = 25°C (unless otherwise specified)

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	Parameter	Min	Тур	Max	Units	Test Conditions	
t _{rr}	Reverse Recovery Time		30			$I_F = 1.0A$, $di_f/dt = 200A/\mu s$, $V_R = 30V$	
t _{rr1}	See Fig. 5, 10		90	135	ns	T _J = 25°C	
t _{rr2}			164	245]	T _J = 125°C	I _F = 16A
I _{RRM1}	Peak Recovery Current		5.8	10	Α	T _J = 25°C	
I _{RRM2}	See Fig. 6		8.3	15	^	T _J = 125°C	V _R = 200V
Q _{rr1}	Reverse Recovery Charge		260	675	nC	T _J = 25°C]
Q _{rr2}	See Fig. 7		680	1838	'''	T _J = 125°C	di _f /dt = 200A/µs
di _{(rec)M} /dt1	Peak Rate of Fall of Recovery Current		120		A/us	T _J = 25°C	
di _{(rec)M} /dt2	During t _b See Fig. 8		76		γνμο	T _J = 125°C	

Thermal - Mechanical Characteristics

	Parameter	Min	Тур	Max	Units
T _{lead} ①	Lead Temperature			300	°C
RthJC	Thermal Resistance, Junction to Case			0.83	
R _{thJA} ②	Thermal Resistance, Junction to Ambient			80	K/W
R _{thCS} ③	Thermal Resistance, Case to Heat Sink		0.50		
Wt	Weight		2.0		g
			0.07		(oz)
	Mounting Torque	6.0		12	Kg-cm
		5.0		10	lbf•in

 $^{\, \}oplus \,$ 0.063 in. from Case (1.6mm) for 10 sec

Typical Socket Mount Mounting Surface, Flat, Smooth and Greased

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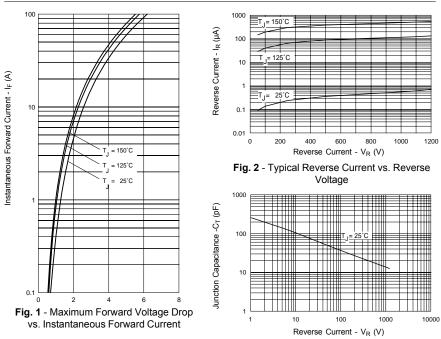


Fig. 3 - Typical Junction Capacitance vs. Reverse Voltage

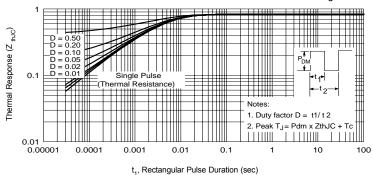
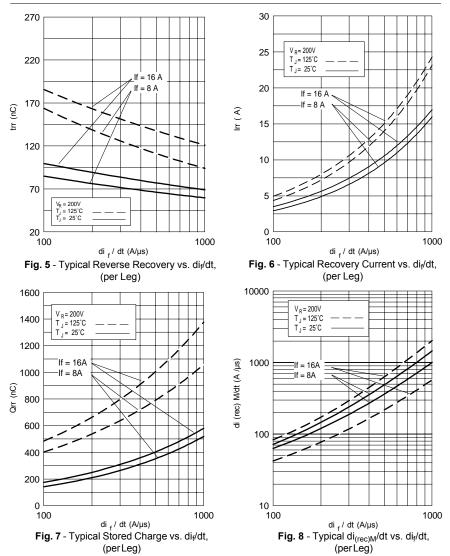


Fig. 4 - Maximum Thermal Impedance Z_{thjc} Characteristics

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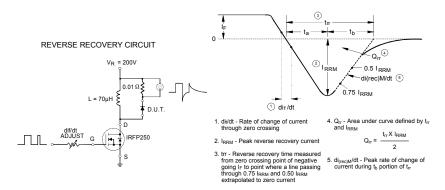
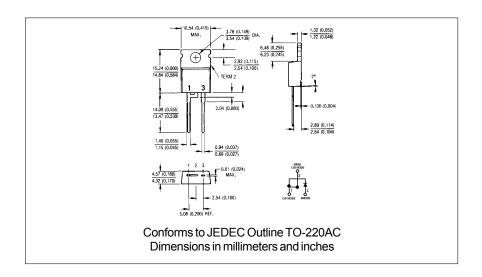


Fig. 9 - Reverse Recovery Parameter Test Circuit

Fig. 10 - Reverse Recovery Waveform and Definitions

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Data and specifications subject to change without notice.